

STPS10M80C

Power Schottky rectifier

Features

- High junction temperature capability
- Optimized trade-off between leakage current and forward voltage drop
- Low leakage current
- Avalanche capability specified
- Insulated package TO-220FPAB
 - insulated voltage: 2000 V
 - package capacitance: 45 pF

Description

This dual diode Schottky rectifier is suited for high frequency switch mode power supply.

Packaged in TO-220AB, I²PAK, D²PAK and TO-220FPAB, this device is particularly suited for use in notebook, game station, LCD TV and desktop adapters, providing these applications with a good efficiency at both low and high load.

Table 1. Device summary

Symbol	Value
I _{F(AV)}	2 x 5 A
V _{RRM}	80 V
T _j (max)	175 °C
V _F (typ)	465 mV

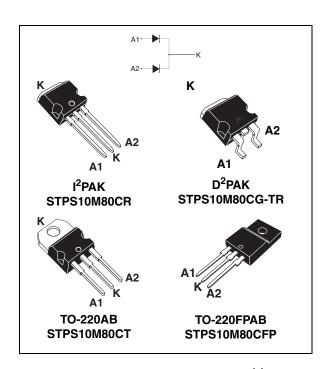
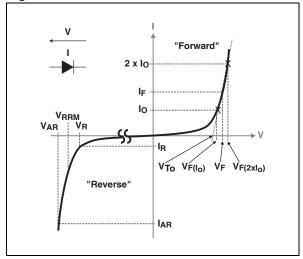


Figure 1. Electrical characteristics^(a)



a. V_{ARM} and I_{ARM} must respect the reverse safe operating area defined in *Figure 13*. V_{AR} and I_{AR} are pulse measurements ($t_p < 1~\mu s$). V_R , I_R , V_{RRM} and V_F , are static characteristics

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1 Characteristics

Table 2. Absolute ratings (limiting values, per diode, at $T_{amb} = 25$ °C unless otherwise specified)

Symbol	Parameter			Value	Unit	
V _{RRM}	Repetitive peak reverse vol	tage			80	V
I _{F(RMS)}	Forward rms current				30	Α
	Average forward current,	TO-220AB, I ² PAK, D ² PAK	T _c = 160 °C T _c = 160 °C	Per diode Per device	5 10	^
$\delta = 0.5$	TO-220FPAB	T _c = 150 °C T _c = 140 °C		5 10	Α	
I _{FSM}	Surge non repetitive forward current	$t_p = 10 \text{ ms sinusoidal}$ $T_c = 25 ^{\circ}\text{C}$			150	Α
P _{ARM} ⁽¹⁾	Repetitive peak avalanche	power	$T_j = 25$ °C, $t_p = 1$ μs			W
V _{ARM} ⁽²⁾	Maximum repetitive peak avalanche voltage	t _p < 1 μs, T _j < 150 °C, I _{AR} < 12 A			100	V
V _{ASM} ⁽²⁾	Maximum single pulse peak avalanche voltage	t _p < 1 μs, T _j < 150 °C, I _{AR} < 12 A			100	V
T _{stg}	Storage temperature range			-65 to +175	°C	
T _j	Maximum operating junction temperature ⁽³⁾			175	ç	

For temperature or pulse time duration deratings, please refer to figure 3 and 4. More details regarding the avalanche energy measurements and diode validation in the avalanche are provided in the application notes AN1768 and AN2025.

Table 3. Thermal parameters

Symbol	Parameter			Value	Unit
		TO-220AB		3.10	
В	$R_{th(j-c)}$ Junction to case $ \frac{I^2PAK, D^2PAK}{TO-220FPAB} $	total	1.88	°C/W	
□th(j-c)		TO-220FPAB	per diode	5.90	C/VV
			total	4.75	
R _{th(c)}	Coupling	TO-220AB I ² PAK, D ² PAK		0.65	°C/W
		TO-220FPAB		3.60	

When the two diodes 1 and 2 are used simultaneously:

$$\Delta T_{j}(diode\ 1) = P(diode\ 1)\ x\ R_{th(j-c)}(Per\ diode) + P(diode\ 2)\ x\ R_{th(c)}$$

^{2.} See Figure 13

^{3.} $\frac{dPtot}{dTj} < \frac{1}{Rth(j-a)}$ condition to avoid thermal runaway for a diode on its own heatsink

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Table 4.	Static electrical	characteristics ((per diode)
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Symbol	Parameter	Test conditions		Min.	Тур.	Max.	Unit
I _R ⁽¹⁾	Reverse leakage current	T _j = 25 °C		-	4	20	μΑ
'R`	Heverse leakage current	T _j = 125 °C		-	3.5	15	mA
		T _j = 25 °C	-	0.540	0.580		
	Forward voltage drop $T_{j} = 125 \text{ °C}$ $T_{j} = 25 \text{ °C}$ $T_{j} = 125 \text{ °C}$ $T_{j} = 25 \text{ °C}$	T _j = 125 °C	I _F = 2.5 A	-	0.465	0.495	
V _E ⁽²⁾		T _j = 25 °C		-	0.640	0.705	V
VF` ′		T _j = 125 °C	I _F = 5 A	-	0.550	0.590	V
		L = 10 A	-	0.775	0.850		
		T _j = 125 °C	$T_j = 125 ^{\circ}\text{C}$ $I_F = 10 \text{A}$	-	0.635	0.705	

- 1. Pulse test: t_p = 5 ms, δ < 2 %
- 2. Pulse test: t_p = 380 μ s, δ < 2 %

To evaluate the conduction losses use the following equation:

 $P = 0.475 \times I_{F(AV)} + 0.023 \times I_{F}^{2}_{(RMS)}$

Figure 2. Average forward power dissipation Figure 3. Average forward current versus average forward current (per diode) Figure 3. Average forward current ambient temperature ($\delta = 0.5$, per diode)

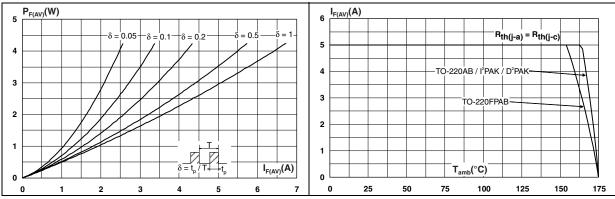
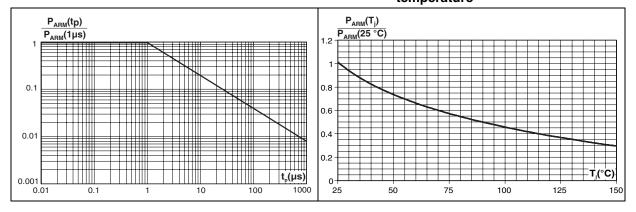


Figure 4. Normalized avalanche power derating versus pulse duration

Figure 5. Normalized avalanche power derating versus junction temperature



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Figure 6. Non repetitive surge peak forward current versus overload duration (maximum values, per diode)

Figure 7. Non repetitive surge peak forward current versus overload duration (maximum values, per diode)

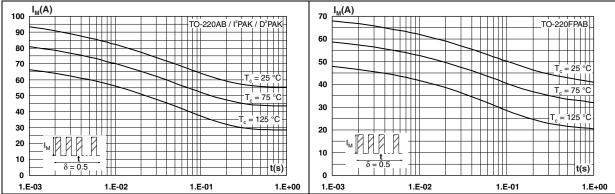


Figure 8. Relative thermal impedance junction to case versus pulse duration

Figure 9. Relative thermal impedance junction to case versus pulse duration (TO-220FPAB)

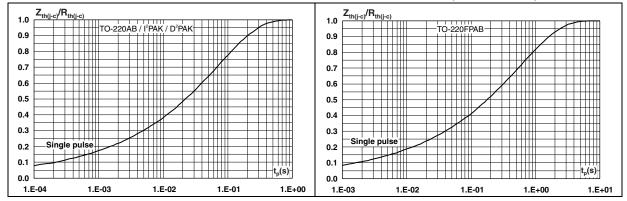
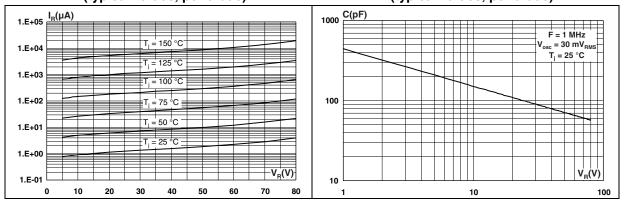


Figure 10. Reverse leakage current versus reverse voltage applied (typical values, per diode)

Figure 11. Junction capacitance versus reverse voltage applied (typical values, per diode)

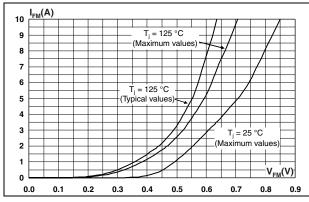


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Figure 12. Forward voltage drop versus forward current (per diode)

Figure 13. Reverse safe operating area $(t_p < 1 \mu s \text{ and } T_i < 150 \text{ °C})$



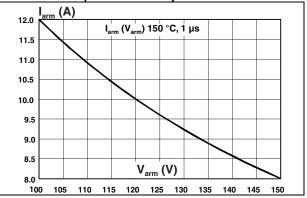
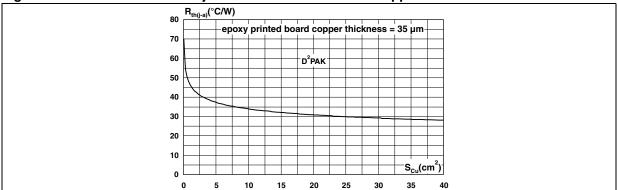


Figure 14. Thermal resistance junction to ambient versus copper surface under tab for D²PAK

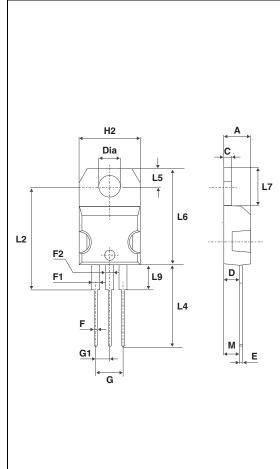


2 Package information

- Epoxy meets UL94, V0
- Cooling method: by conduction (C)
- Recommended torque value: 0.4 to 0.6 N⋅m

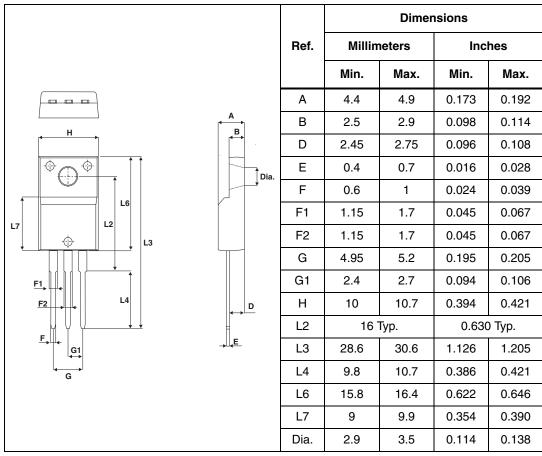
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Table 5. TO-220AB dimensions



	Dimensions			
Ref.	Millimeters		Inc	hes
	Min.	Max.	Min.	Max.
Α	4.40	4.60	0.173	0.181
С	1.23	1.32	0.048	0.051
D	2.40	2.72	0.094	0.107
Е	0.49	0.70	0.019	0.027
F	0.61	0.88	0.024	0.034
F1	1.14	1.70	0.044	0.066
F2	1.14	1.70	0.044	0.066
G	4.95	5.15	0.194	0.202
G1	2.40	2.70	0.094	0.106
H2	10	10.40	0.393	0.409
L2	16.4	Тур.	0.645 Typ.	
L4	13	14	0.511	0.551
L5	2.65	2.95	0.104	0.116
L6	15.25	15.75	0.600	0.620
L7	6.20	6.60	0.244	0.259
L9	3.50	3.93	0.137	0.154
М	2.6 Typ.		0.102	2 Тур.
Dia.	3.75	3.85	0.147	0.151

Table 6. TO-220FPAB dimensions



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Table 7. D²PAK dimensions

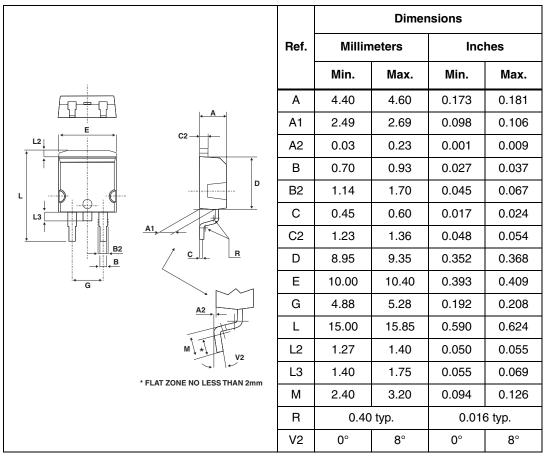
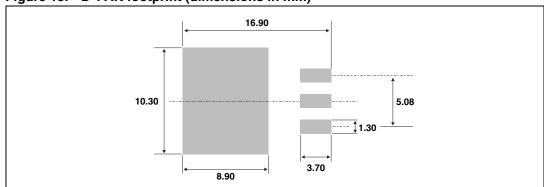
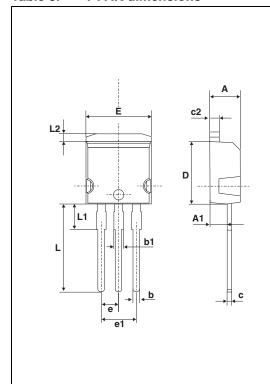


Figure 15. D²PAK footprint (dimensions in mm)



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Table 8. I²PAK dimensions



	Dimensions				
Ref.	Millimeters		Inc	hes	
	Min.	Max.	Min.	Max.	
Α	4.40	4.60	0.173	0.181	
A1	2.40	2.72	0.094	0.107	
b	0.61	0.88	0.024	0.035	
b1	1.14	1.70	0.044	0.067	
С	0.49	0.70	0.019	0.028	
c2	1.23	1.32	0.048	0.052	
D	8.95	9.35	0.352	0.368	
е	2.40	2.70	0.094	0.106	
e1	4.95	5.15	0.195	0.203	
Е	10	10.40	0.394	0.409	
L	13	14	0.512	0.551	
L1	3.50	3.93	0.138	0.155	
L2	1.27	1.40	0.050	0.055	

3 Ordering information

Table 9. Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
STPS10M80CT	STPS10M80CT	TO-220AB	1.9 g	50	Tube
STPS10M80CFP	STPS10M80CFP	TO-220FPAB	2.0 g	50	Tube
STPS10M80CR	STPS10M80CR	I ² PAK	1.49 g	50	Tube
STPS10M80CG-TR	STPS10M80CG	D ² PAK	1.48 g	1000	Tape and reel

4 Revision history

Table 10. Revision history

Date	Revision	Changes
14-Apr-2011	1	First issue.

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